

FIG. 1

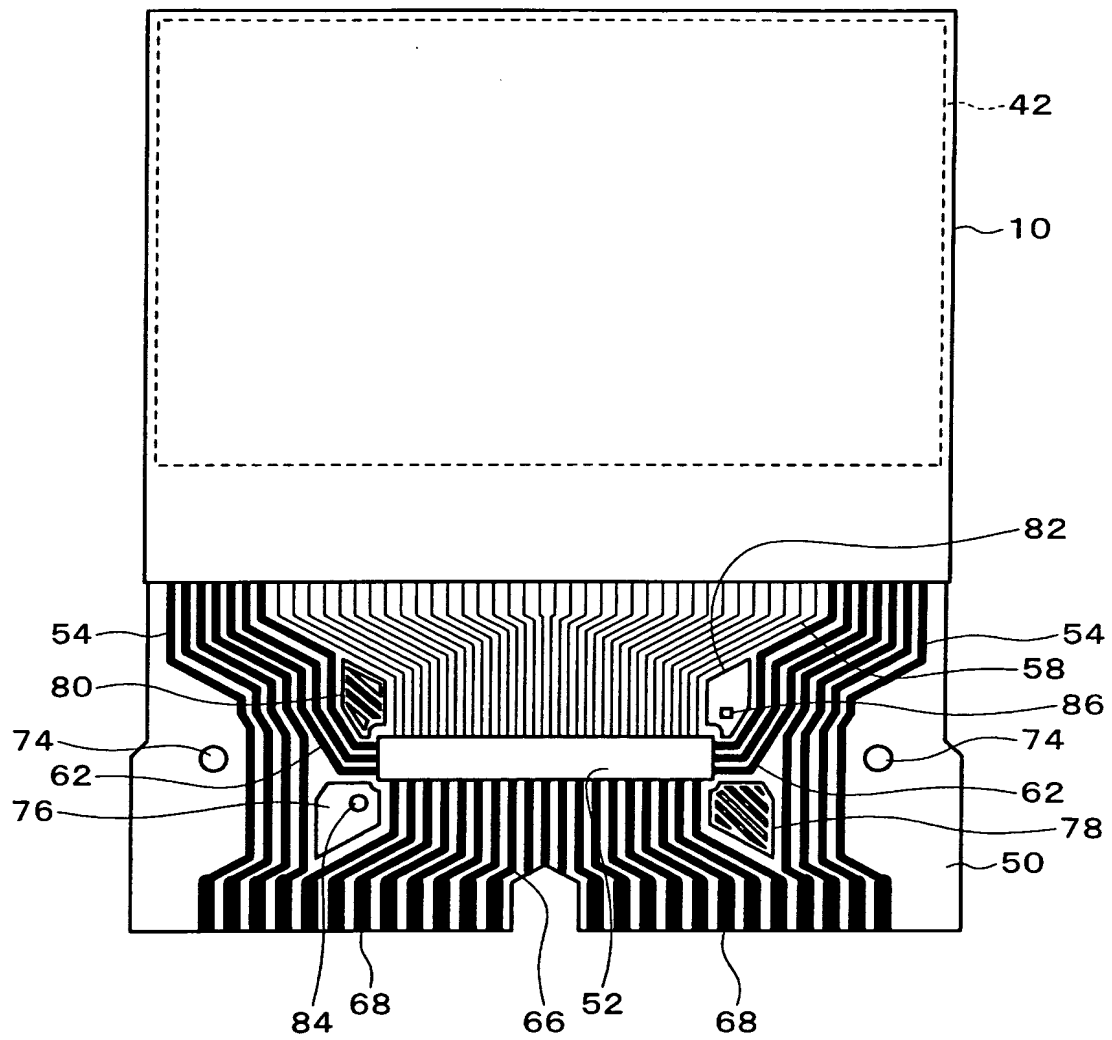


FIG. 2

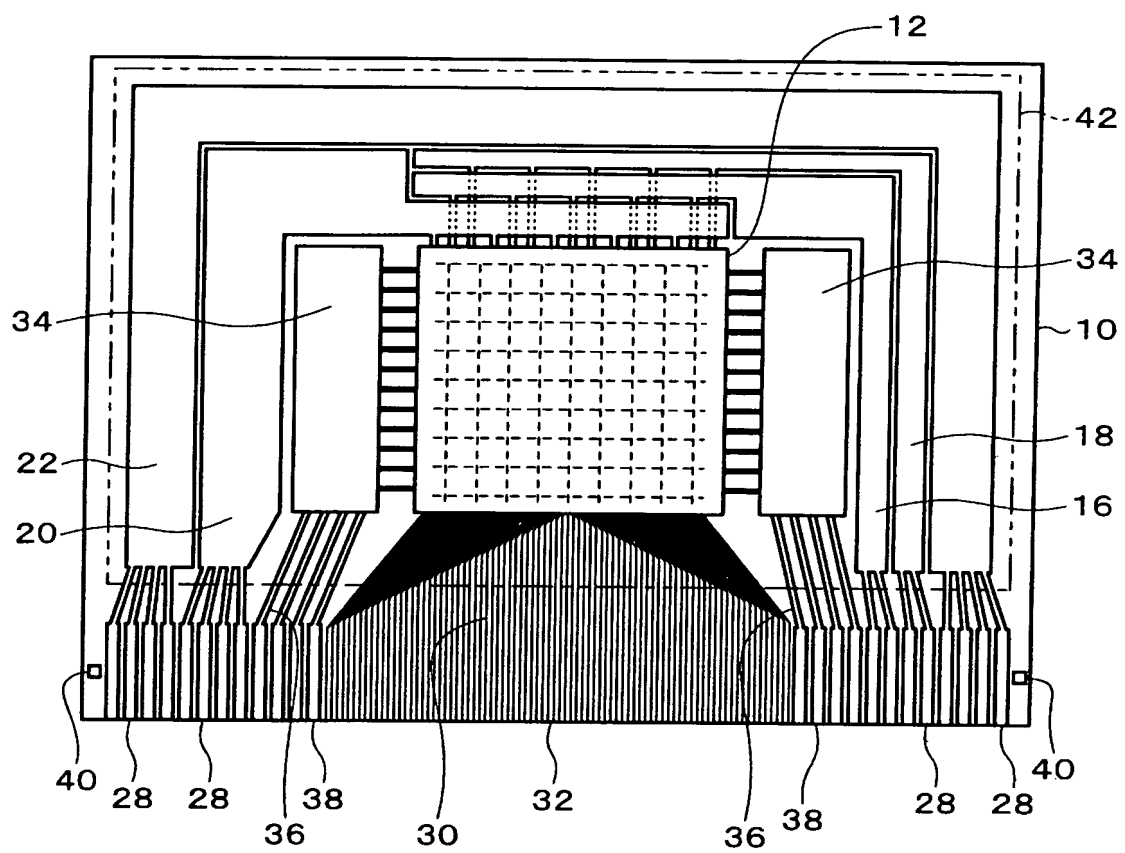


FIG. 3

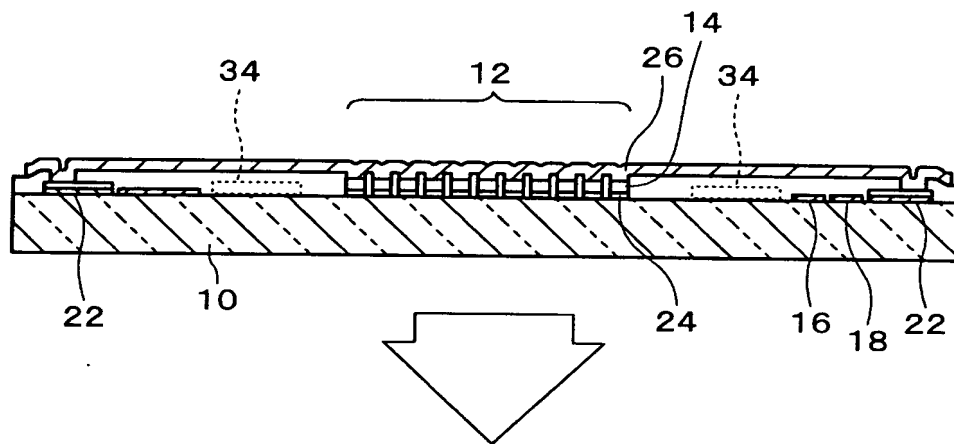


FIG. 4

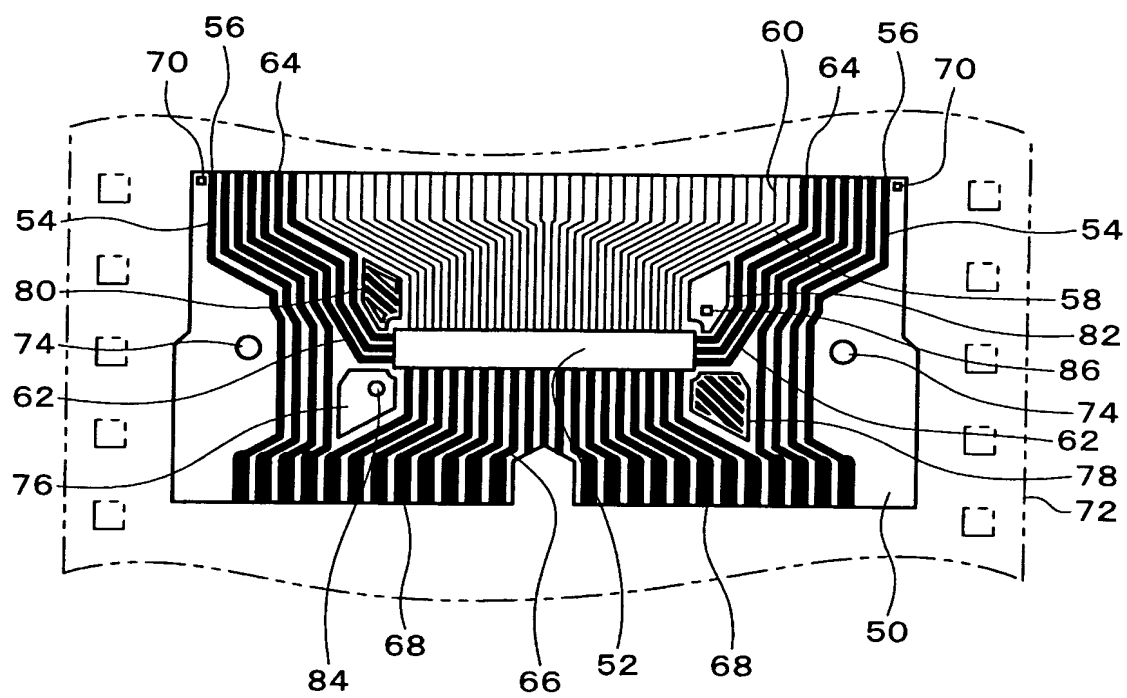


FIG. 6

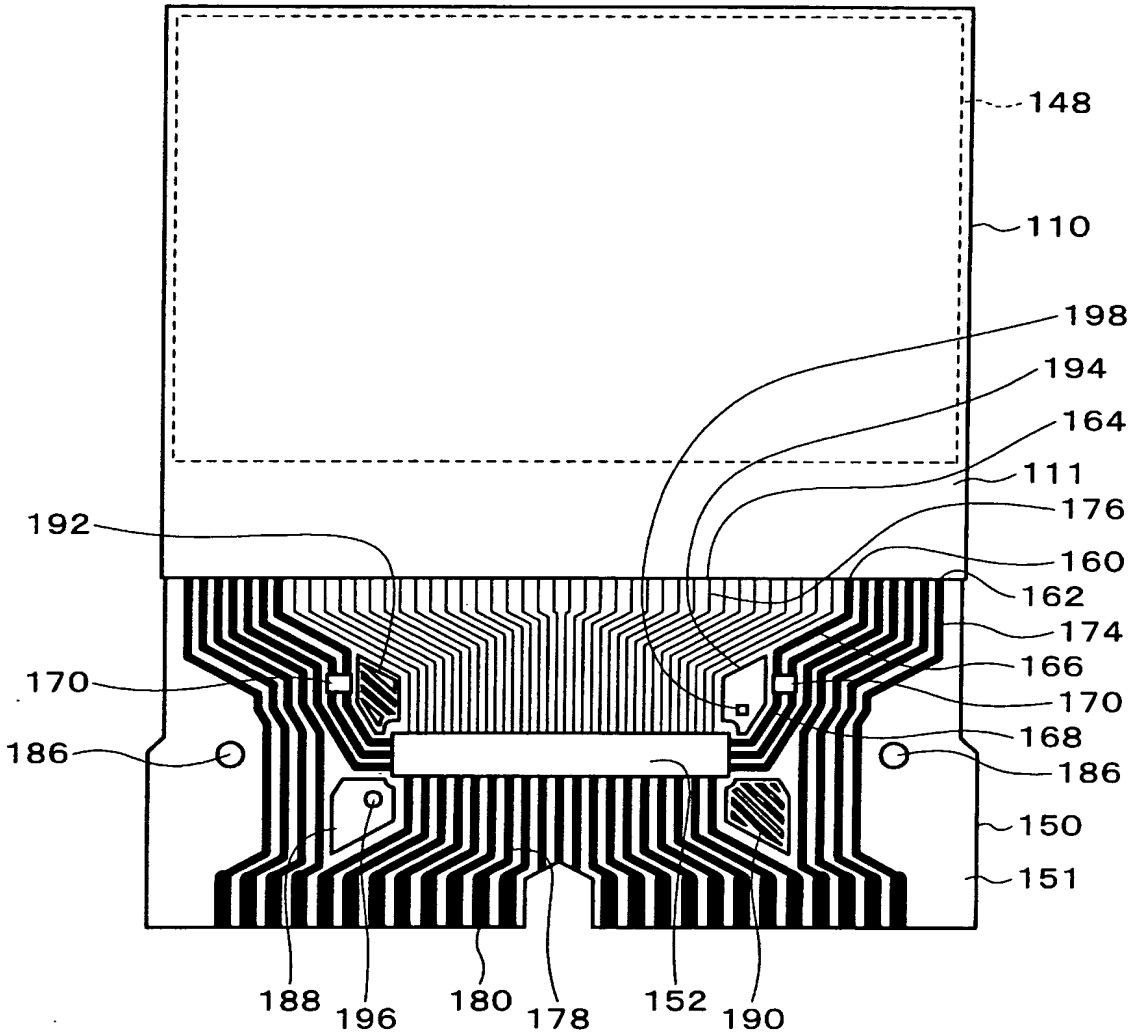


FIG. 7

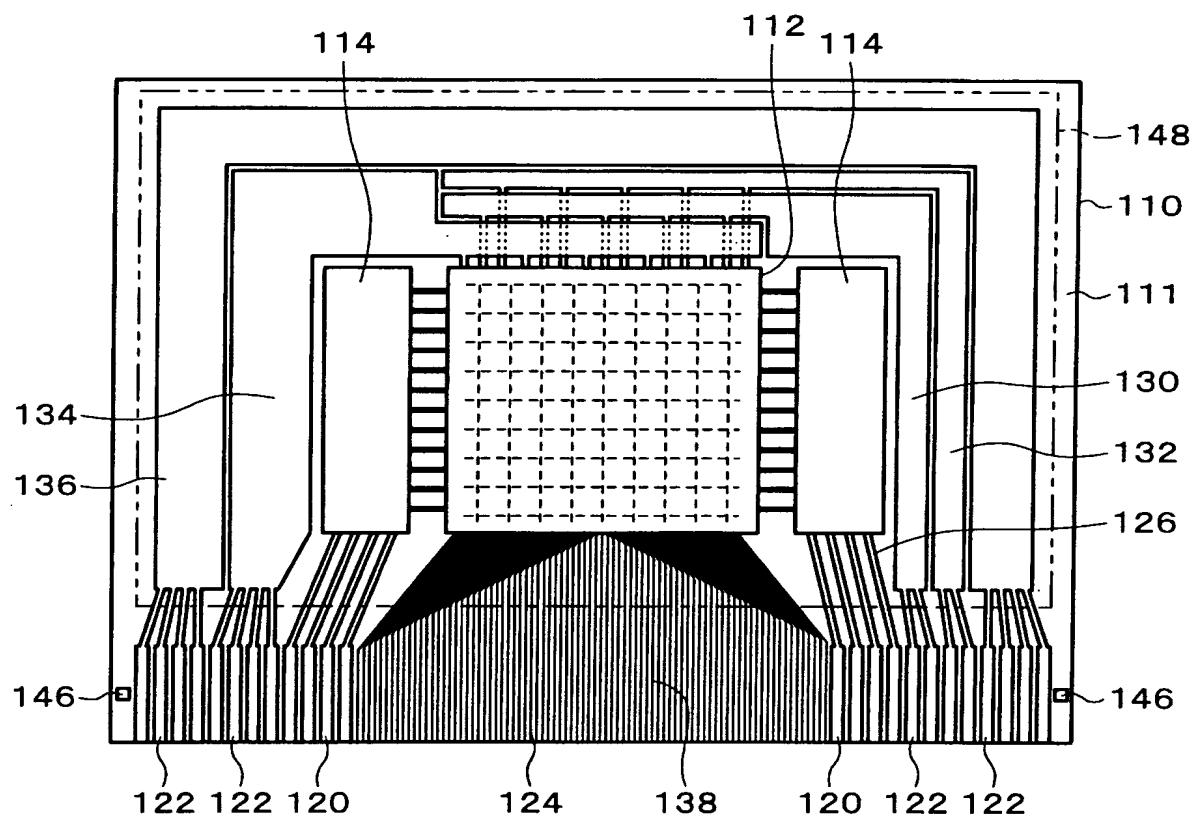


FIG. 8

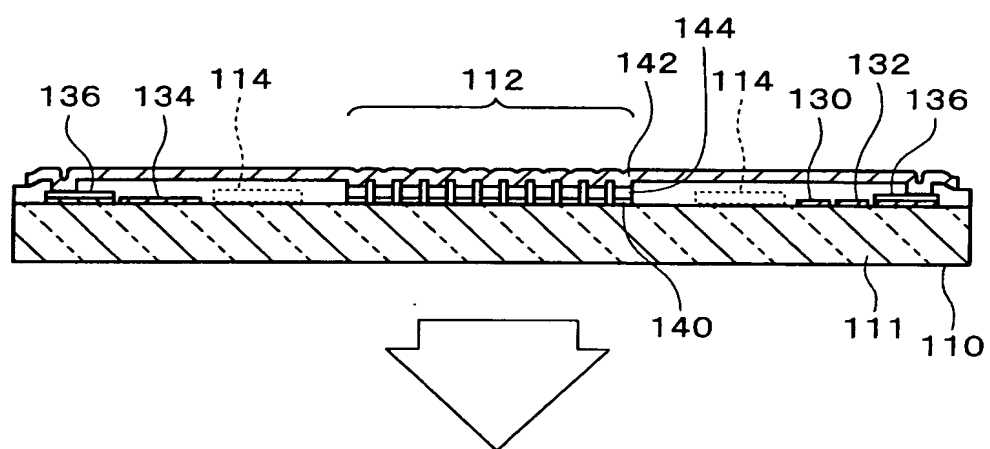


FIG. 9

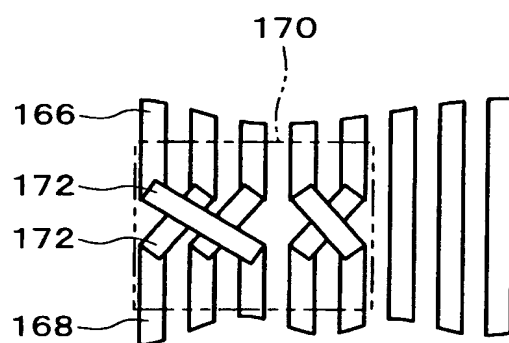


FIG. 10

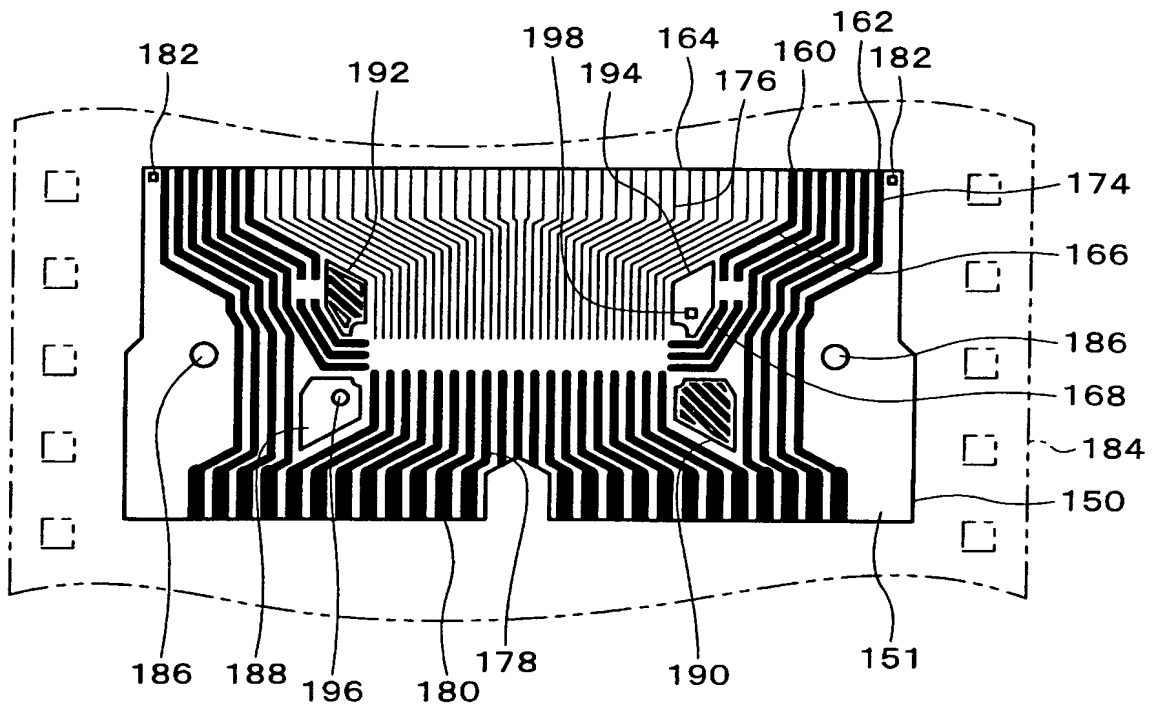


FIG. 11A

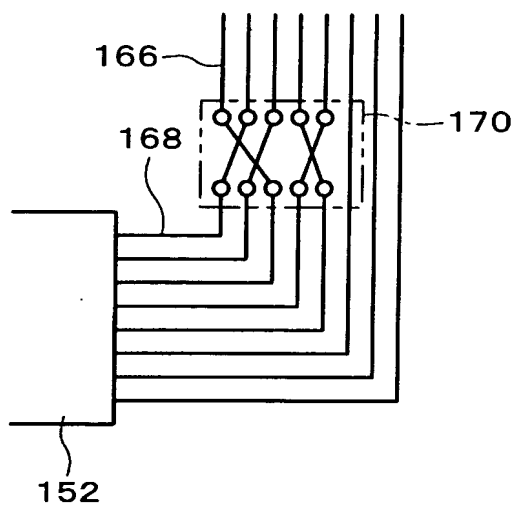


FIG. 11B

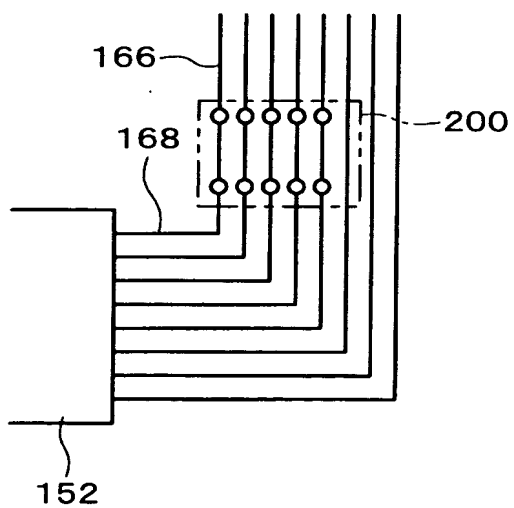


FIG. 12

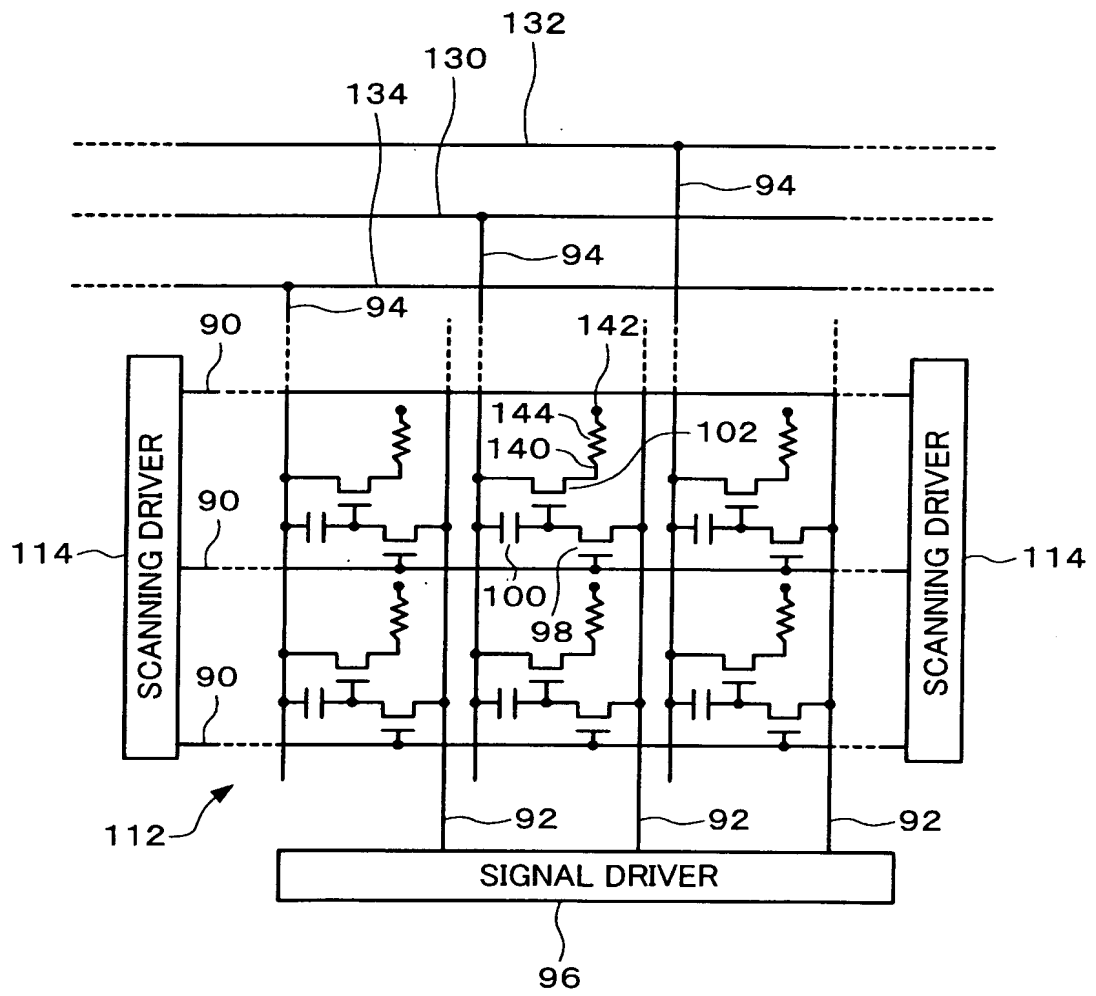
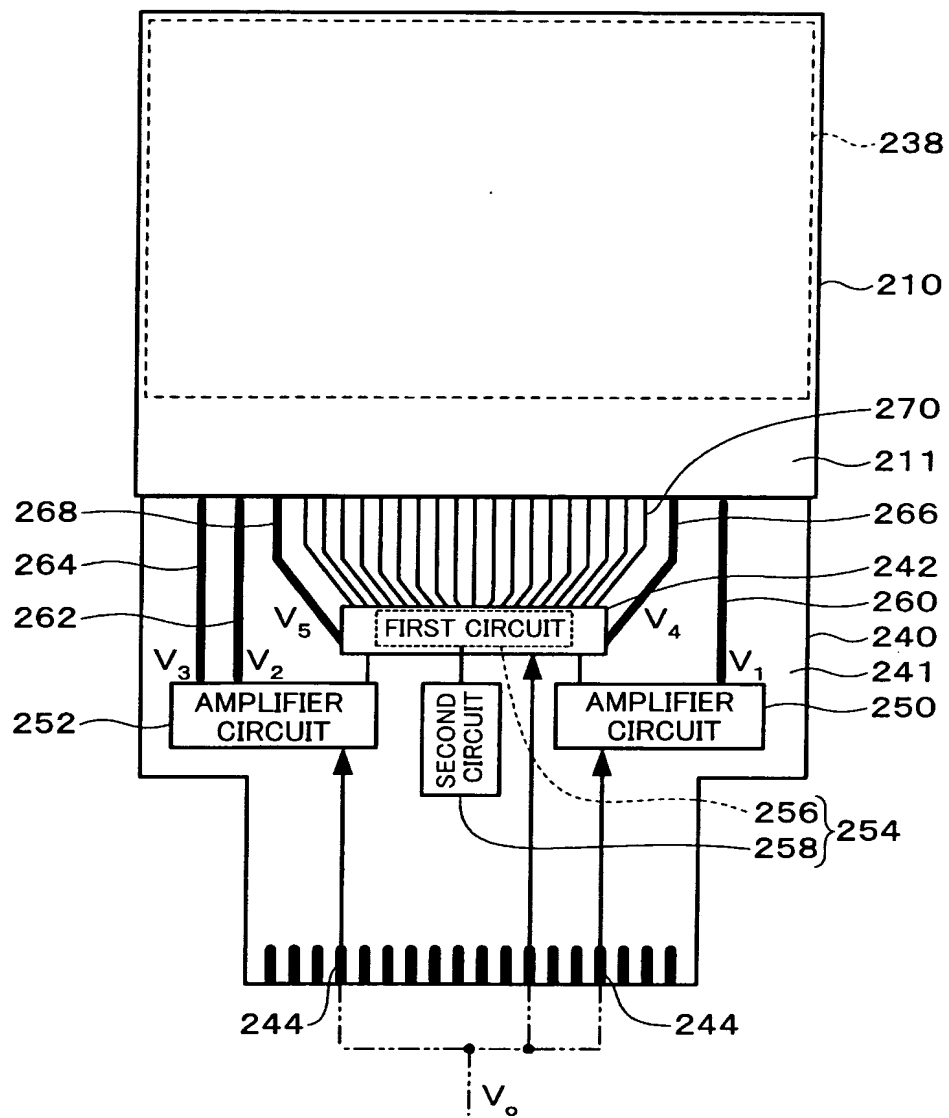


FIG. 13



A cross-sectional view of a semiconductor device. The device features a central region with a grid-like pattern, labeled 210. This central region is flanked by two vertical rectangular blocks, labeled 214. Above the central region, there is a horizontal structure with a grid-like pattern, labeled 212. The entire device is enclosed within a rectangular frame, labeled 238. The bottom of the device shows a series of vertical lines, labeled 228, which are connected to a base layer, labeled 220. The top of the device is labeled 211. The right side of the device is labeled 230. The left side of the device is labeled 222.

FIG. 15

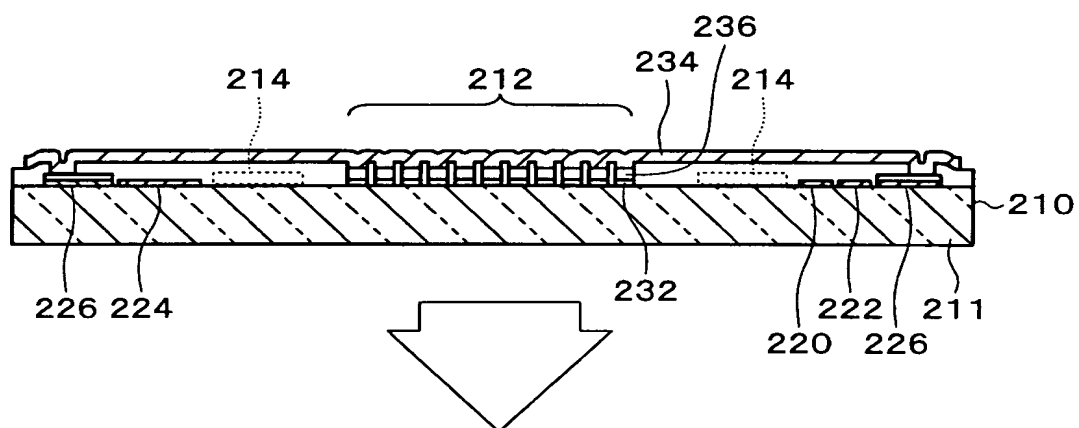


FIG. 16

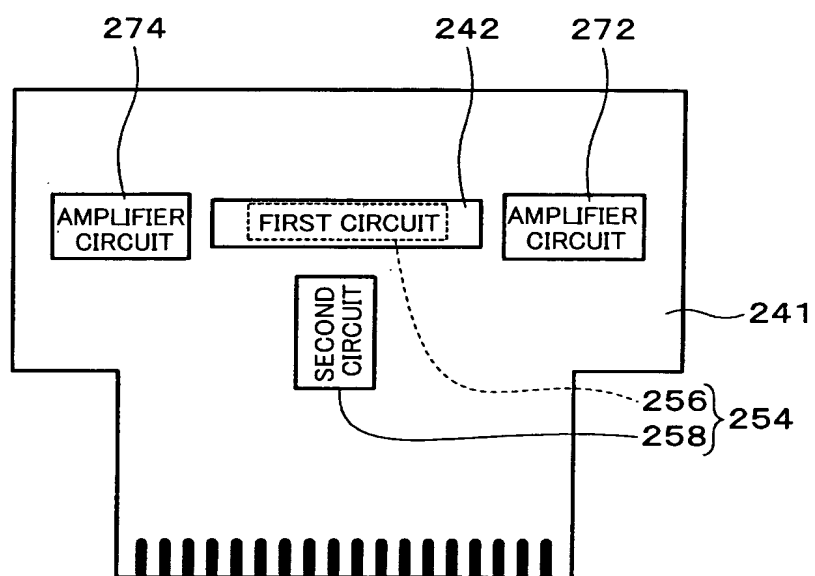


FIG. 17

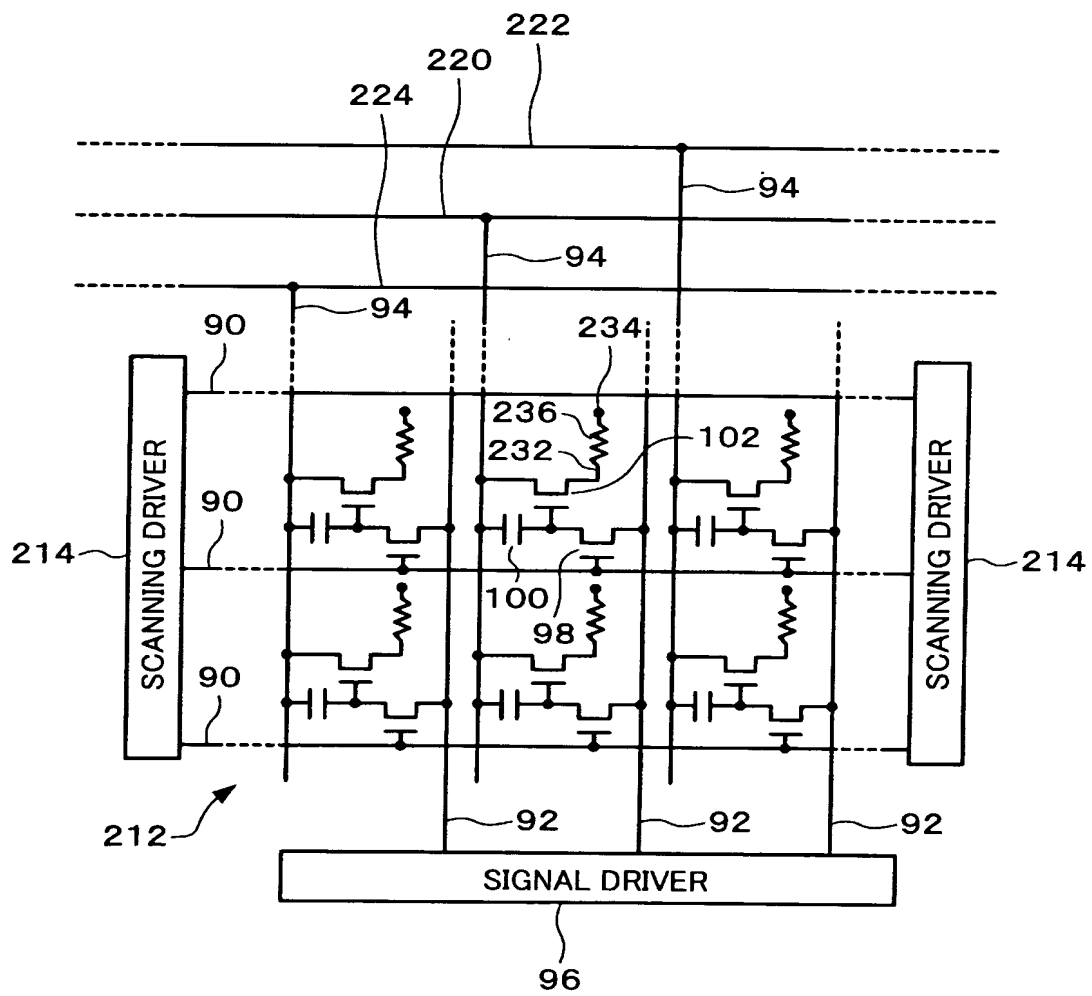


FIG. 18

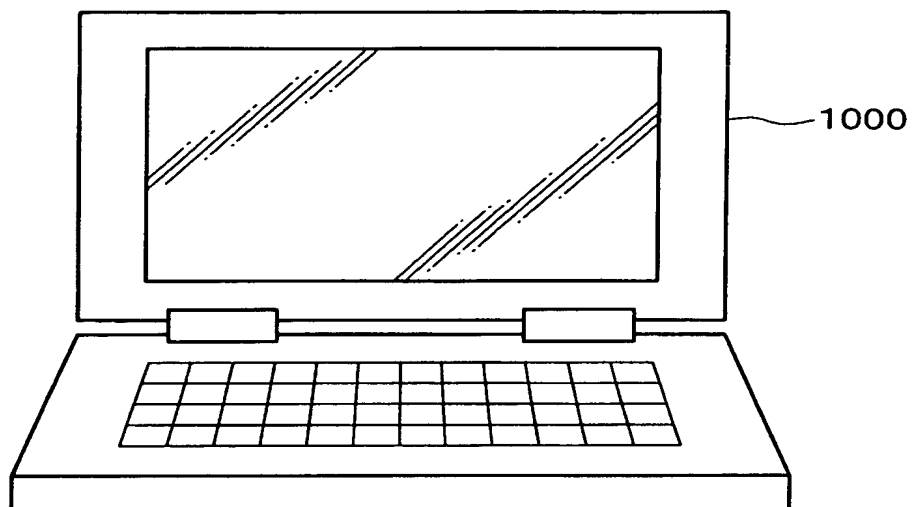


FIG. 19

